

YJ Planar Schottky Barrier Diode Die Specification

60V 5A, 70mil, Schottky barrier diode die based on silicon planar process
Part No.: PSB070M060SS-280A

Main Products Characterstics

- Average forward current: IF(AV) = 5 A
- Maximum operating junction temperature: Tj = 150 °C
- ESD rating: >8KV, per IEC61000-4-2 (Contact Discharge)
- Top metal: Ag

Maximum Ratings

Rating
Reverse Voltage
Forward Current
Reverse Leakage Current
Power Dissipation
Operating Temperature
Storage Temperature
Die Temperature

Static Electrical Characteristics (Ta = 25°C)

Symbol	Test Condition	Value
V _{BR}	I _F = 5 A	60 V
I _F	Pulse Test: tp = 300 μs, δ ≤ 2%	5 A
I _R	V _R = 60 V	10 μA

Device Schematics and Outline Drawing

Die Thickness *	70 mil
Die Size **	0.5mm x 0.5mm
Top Metal Pad	0.1mm x 0.1mm
Active Area	0.3mm x 0.3mm
Top Metal	Ag
Back Metal	Ag
Note: 1 * : Also can offer device with 8 mils thickness	
2 **: Cutting street width is around 1.5 mils	

Important Notice

Specification apply to die only. Actual performance may degrade when assembled.	Recommended Storage Environment:
does not guarantee device performance after assembly.	Store in original container, in dessicated nitrogen, with no contamination.
All operating parameters must be validated for each customer application by customer's technical experts.	Shelf life for parts stored in above condition is 2 years.
Data sheet information is subjected to change without notice.	If the storage is done in normal atmosphere shelf life is reduced to 6 months.

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